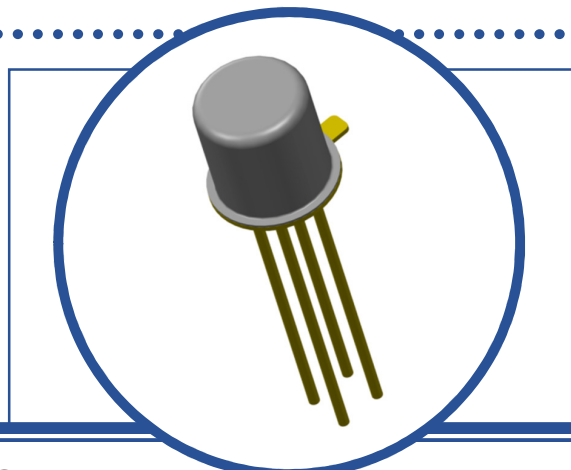


SILICON SMALL SIGNAL N-CHANNEL JFET

2N4416/ 2N4416A

- Low Noise, High Gain.
- Hermetic 4 Pin TO-72 Package.
- Designed For VHF/UHF Amplifiers, Oscillators And Mixers.
- Screening Options Available.



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

| | | 2N4416 | 2N4416A |
|------------------|---|---------------|----------|
| V _{DS} | Drain – Source Voltage | 30V | 35V |
| V _{GS} | Gate – Source Voltage | -30V | -35V |
| V _{GD} | Gate – Drain Voltage | -30V | -35V |
| I _G | Gate Current | 10mA | |
| P _D | Total Power Dissipation at T _A = 25°C Derate Above 25°C | 300mW | 2.4mW/°C |
| T _J | Junction Temperature Range | -65 to +150°C | |
| T _{stg} | Storage Temperature Range | -65 to +200°C | |

THERMAL PROPERTIES (Each Device)

| Symbols | Parameters | Max. | Units |
|------------------|---|------|-------|
| R _{θJA} | Thermal Resistance, Junction To Ambient | 417 | °C/W |

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



SILICON SMALL SIGNAL N-CHANNEL JFET 2N4416 / 2N4416A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

| Symbols | Parameters | Test Conditions | | Min. | Typ | Max. | Units |
|-----------------|---------------------------------|-------------------------|---------------------------|------|-----|------|----------|
| $V_{(BR)GSS}$ | Gate – Source Breakdown Voltage | $V_{DS} = 0$ | 2N4416 | -30 | | | V |
| | | $I_G = -1.0\mu\text{A}$ | 2N4416A | -35 | | | |
| $V_{GS(off)}$ | Gate – Source Cut-off Voltage | $V_{DS} = 15\text{V}$ | 2N4416 | | | -6 | |
| | | $I_D = 1.0\text{nA}$ | 2N4416A | -2.5 | | -6 | |
| V_{GS} | Gate – Source Voltage | $V_{DS} = 15\text{V}$ | $I_D = 0.5\mu\text{A}$ | -1.0 | | -5.5 | |
| $I_{DSS}^{(1)}$ | Saturation Drain Current | $V_{DS} = 15\text{V}$ | $V_{GS} = 0$ | 5 | | 15 | mA |
| I_{GSS} | Gate Reverse Current | $V_{DS} = 0$ | $V_{GS} = -20\text{V}$ | | | -100 | pA |
| | | | $T_A = 150^\circ\text{C}$ | | | -100 | nA |
| I_G | Gate Operating Current | $V_{DG} = 10\text{V}$ | $I_D = 1.0\text{mA}$ | | -20 | | pA |
| $I_D(off)$ | Drain Cut-off Current | $V_{DS} = 10\text{V}$ | $V_{GS} = -10\text{V}$ | | 2 | | |
| $V_{GS(F)}$ | Gate – Source Forward Voltage | $V_{DS} = 0$ | $I_G = 1.0\text{mA}$ | | 0.7 | 1.0 | V |
| $R_{DS(on)}$ | Drain – Source On Resistance | $V_{GS} = 0$ | $I_D = 1.0\text{mA}$ | | 150 | | Ω |

DYNAMIC CHARACTERISTICS

| | | | | | | | | |
|-------------------|--|--|--------------|-----|---|-----|--------------------------------------|---------------|
| $g_{fs}^{(1)}$ | Common – Source Forward Transconductance | $V_{DS} = 15\text{V}$ $f = 1.0\text{kHz}$ | $V_{GS} = 0$ | 4.5 | | 7.5 | mS | |
| $g_{os}^{(1)}$ | Common – Source Output Transconductance | | | | | | 50 | μS |
| C_{iss} | Common – Source Input Capacitance | $V_{DS} = 15\text{V}$ $f = 1.0\text{MHz}$ | $V_{GS} = 0$ | | | 4 | pF | |
| C_{oss} | Common – Source Output Capacitance | | | | | | | 2 |
| C_{rss} | Common – Source Reverse Transfer Capacitance | | | | | | | 1.2 |
| $\bar{e}_n^{(2)}$ | Equivalent Input Noise Voltage | $V_{DS} = 10\text{V}$ $f = 1.0\text{kHz}$ | $V_{GS} = 0$ | | 6 | | $\frac{\text{nV}}{\sqrt{\text{Hz}}}$ | |

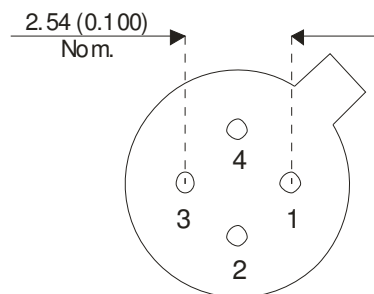
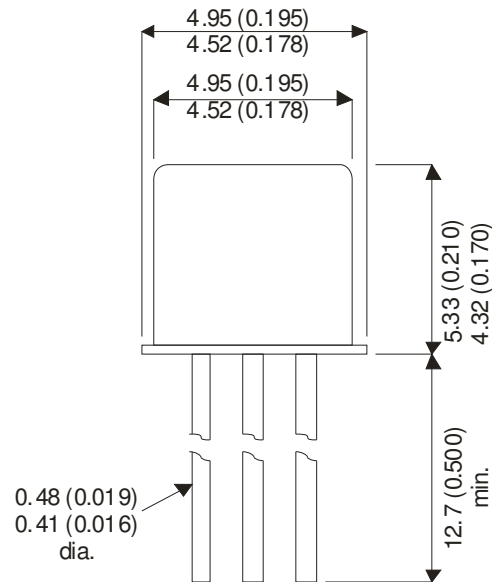
Notes

- (1) Pulse Width $\leq 380\mu\text{s}$, $\delta \leq 2\%$
(2) By design only, not a production test.

SILICON SMALL SIGNAL N-CHANNEL JFET 2N4416 / 2N4416A

MECHANICAL DATA

Dimensions in mm (inches)



TO-72 (TO-206AF)

PIN 1 – CASE

PIN 2 – GATE

PIN 3 – DRAIN

PIN 4 – SOURCE